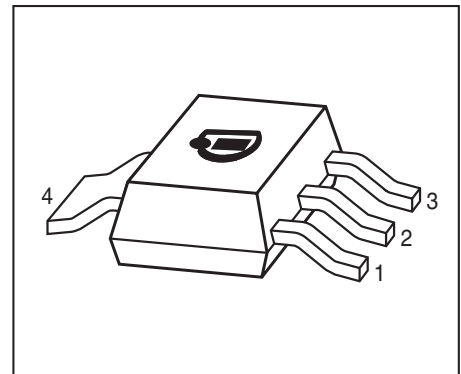


NPN Silicon Darlington Transistor

- For general AF applications
- High collector current
- High current gain
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



Type	Marking	Pin Configuration						Package
PZTA14	PZTA14	1=B	2=C	3=E	4=C	-	-	SOT223

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	30	V
Collector-base voltage	V_{CBO}	30	
Emitter-base voltage	V_{EBO}	10	
Collector current	I_C	300	mA
Peak collector current, $t_p \leq 10$ ms	I_{CM}	500	
Base current	I_B	100	
Peak base current	I_{BM}	200	
Total power dissipation- $T_S \leq 124$ °C	P_{tot}	1.5	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 17	K/W

¹⁾For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

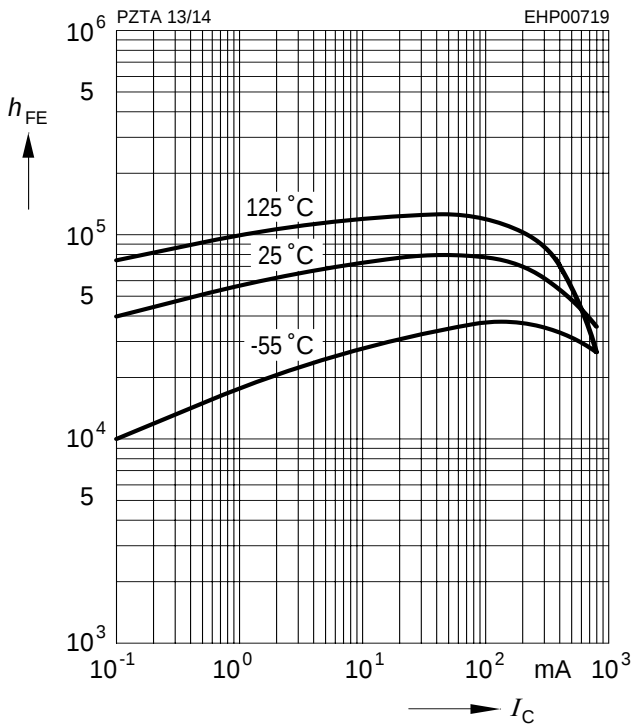
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-base breakdown voltage $I_C = 100\ \mu\text{A}$, $I_E = 0$	$V_{(\text{BR})\text{CBO}}$	30	-	-	V
Collector-emitter breakdown voltage $I_C = 100\ \mu\text{A}$, $V_{\text{BE}} = 0$	$V_{(\text{BR})\text{CES}}$	30	-	-	
Emitter-base breakdown voltage $I_E = 10\ \mu\text{A}$, $I_C = 0$	$V_{(\text{BR})\text{EBO}}$	10	-	-	
Collector-base cutoff current $V_{\text{CB}} = 30\ \text{V}$, $I_E = 0$ $V_{\text{CB}} = 30\ \text{V}$, $I_E = 0$, $T_A = 150\ ^\circ\text{C}$	I_{CBO}	- -	- -	0.1 10	μA
Emitter-base cutoff current $V_{\text{EB}} = 10\ \text{V}$, $I_C = 0$	I_{EBO}	-	-	100	nA
DC current gain ¹⁾ $I_C = 10\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$ $I_C = 100\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$	h_{FE}	10000 20000	- -	- -	-
Collector-emitter saturation voltage ¹⁾ $I_C = 100\ \text{mA}$, $I_B = 0.1\ \text{mA}$	V_{CEsat}	-	-	1.5	V
Base emitter saturation voltage ¹⁾ $I_C = 100\ \text{mA}$, $I_B = 0.1\ \text{mA}$	V_{BEsat}	-	-	2	
AC Characteristics					
Transition frequency $I_C = 50\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$, $f = 20\ \text{MHz}$	f_T	125	-	-	MHz
Collector-base capacitance $V_{\text{CB}} = 10\ \text{V}$, $f = 1\ \text{MHz}$	C_{cb}	-	3	-	pF

¹⁾Pulse test: $t < 300\ \mu\text{s}$; $D < 2\%$

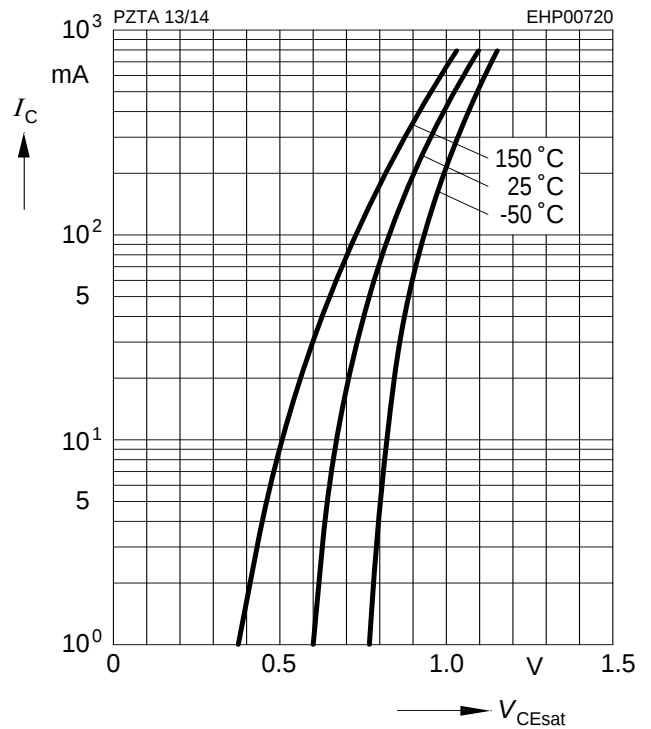
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5 \text{ V}$



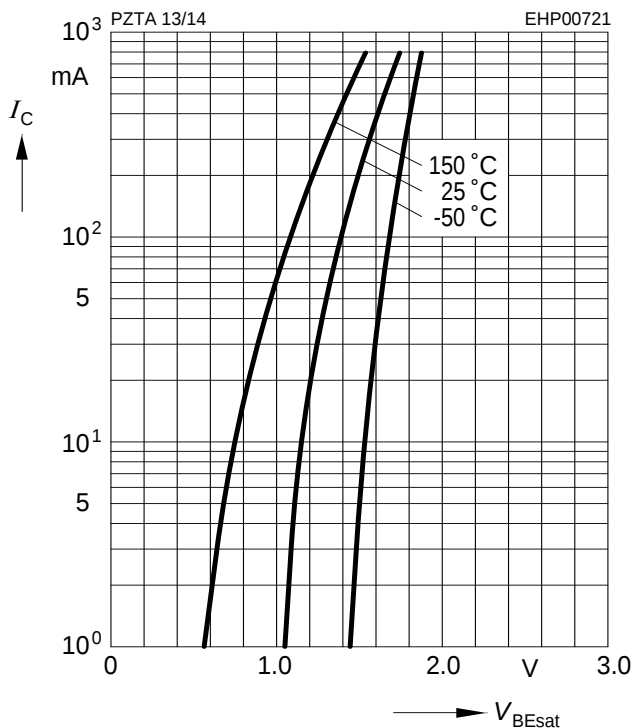
Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 1000$



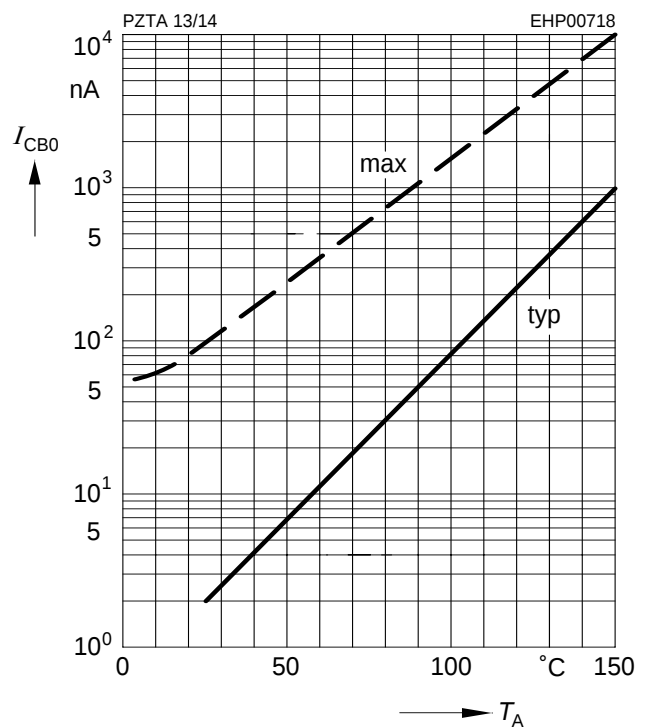
Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 1000$



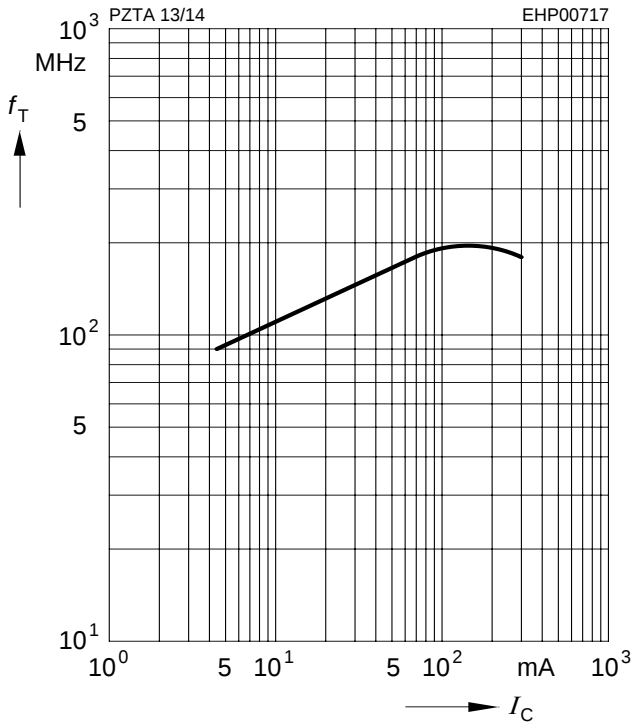
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CBO} = 30 \text{ V}$



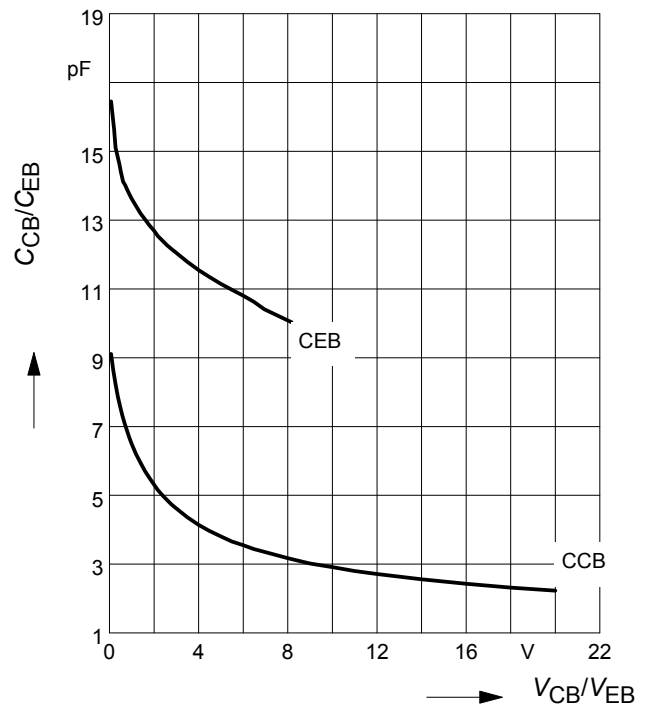
Transition frequency $f_T = f(I_C)$

$V_{CE} = 5 \text{ V}, f = 200 \text{ MHz}$

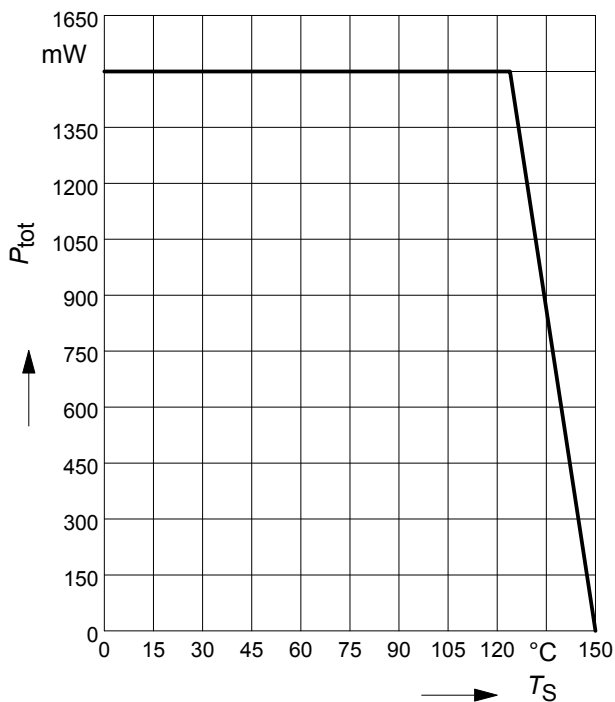


Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$

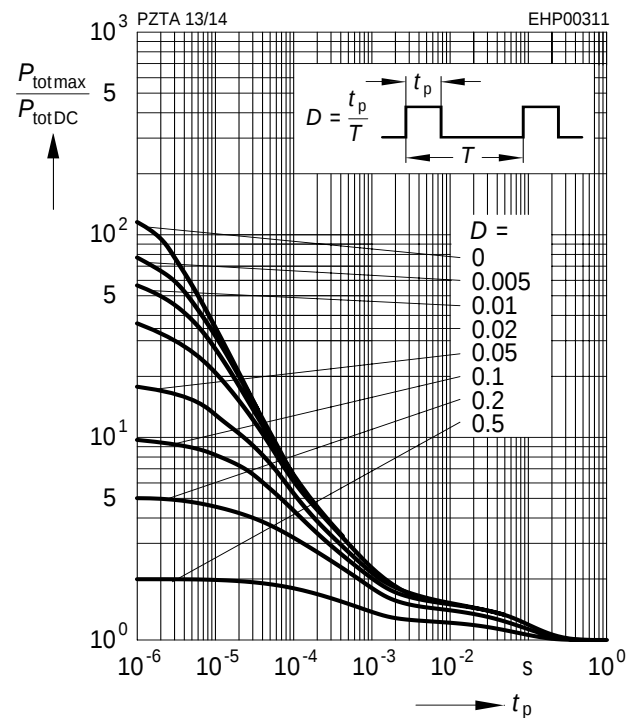


Total power dissipation $P_{tot} = f(T_S)$

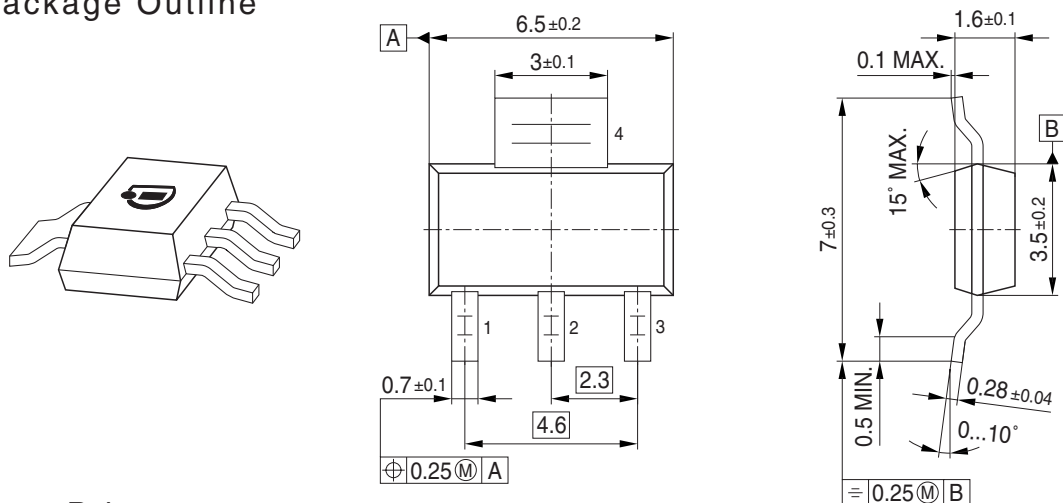


Permissible Pulse Load

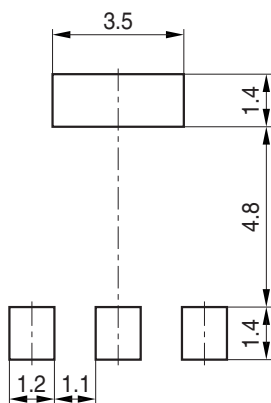
$P_{totmax}/P_{totDC} = f(t_p)$



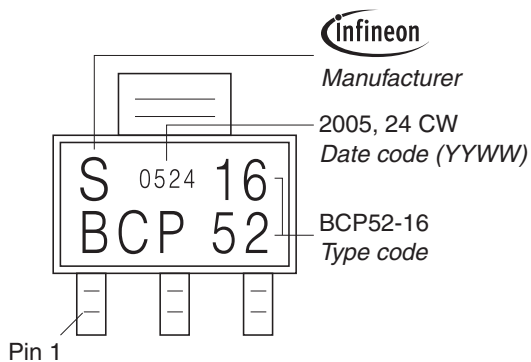
Package Outline



Foot Print

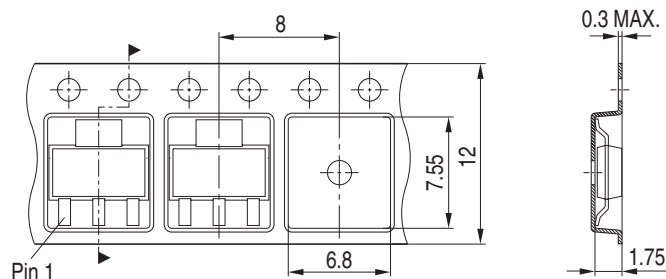


Marking Layout (Example)



Packing

Reel ø180 mm = 1.000 Pieces/Reel
 Reel ø330 mm = 4.000 Pieces/Reel



Edition 2009-11-16

**Published by
Infineon Technologies AG
81726 Munich, Germany**

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